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		Application Number	Not assigned	10/588775	
		Confirmation Number	Not assigned yet		
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		First Named Inventor	Yasuhiro OKAMOTO		
		Art Unit	Not assigned yet 2811		
		Examiner Name	Not assigned yet Meiya Li		
		Attorney Docket Number	Q96219		
Sheet	1	of	1		

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
		US			
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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)			
/M.L./ 		JP	2000-100831	A	04-07-2000		
		JP	2001-308110	A	11-02-2001		
		JP	2004-022773	A	01-22-2004		
		JP	2003-273130	A	09-26-2003		
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		JP	56-088364	A	07-17-1981		
		JP	2744126	B	03-06-1998		

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶
M.L.		J. Li et al. "High Breakdown Voltage GaN HFET with field plate" Electronics Letters, February 1, 2001, Vol. 37 No. 3 p. 196-197.	

Examiner Signature	/Meiya Li/	Date Considered	12/10/2007
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